M5M5V108DFP,VP,KV -70H

1048576-BIT(131072-WORD BY 8-BIT)CMOS STATIC RAM

DESCRIPTION

The M5M5V108DFP,VP,KV are a 1048576-bit CMOS static RAM organized as 131072 word by 8-bit which are fabricated using high-performance triple-polysilicon and double metal CMOS technology. The use of thin film transistor (TFT) load cells and CMOS periphery result in a high density and low power static RAM.

They are low standby current and low operation current and ideal for the battery back-up application.

The M5M5V108DVP,KV are packaged in a 32-pin thin small outline package which is a high reliability and high density surface mount device(SMD).

FEATURES

Type name	Access time (max)	V_{CC}	Power supply current	
			Active (1MHz) (max)	stand-by (max)
M5M5V108DFP,VP,KV-70H	70ns	2.7~3.6V	5mA	12µA

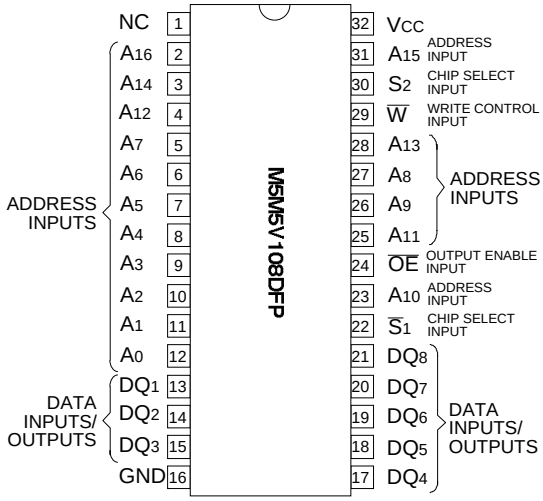
- Directly TTL compatible : All inputs and outputs
- Easy memory expansion and power down by $\overline{S_1}$,S_2
- Data hold on +2V power supply
- Three-state outputs : OR - tie capability
- $\overline{OE}$ prevents data contention in the I/O bus
- Common data I/O
- Package

M5M5V108DFP ·····32pin 525mil SOP
M5M5V108DVP,RV ·····32pin 8 X 20 mm^2 TSOP
M5M5V108DKV,KR ·····32pin 8 X 13.4 mm^2 TSOP

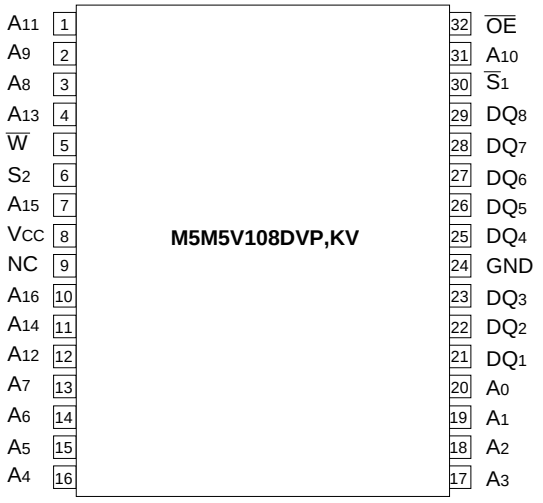
APPLICATION

Small capacity memory units

PIN CONFIGURATION (TOP VIEW)



Outline 32P2M-A



Outline 32P3H-E(VP), 32P3K-B(KV)

NC : NO CONNECTION

FUNCTION

The operation mode of the M5M5V108D series are determined by a combination of the device control inputs $\overline{S}_1$,S_2,$\overline{W}$ and $\overline{OE}$.

Each mode is summarized in the function table.

A write cycle is executed whenever the low level $\overline{W}$ overlaps with the low level $\overline{S}_1$ and the high level S_2. The address must be set up before the write cycle and must be stable during the entire cycle. The data is latched into a cell on the trailing edge of $\overline{W}$,$\overline{S}_1$ or S_2,whichever occurs first,requiring the set-up and hold time relative to these edge to be maintained. The output enable input $\overline{OE}$ directly controls the output stage. Setting the $\overline{OE}$ at a high level, the output stage is in a high-impedance state, and the data bus contention problem in the write cycle is eliminated.

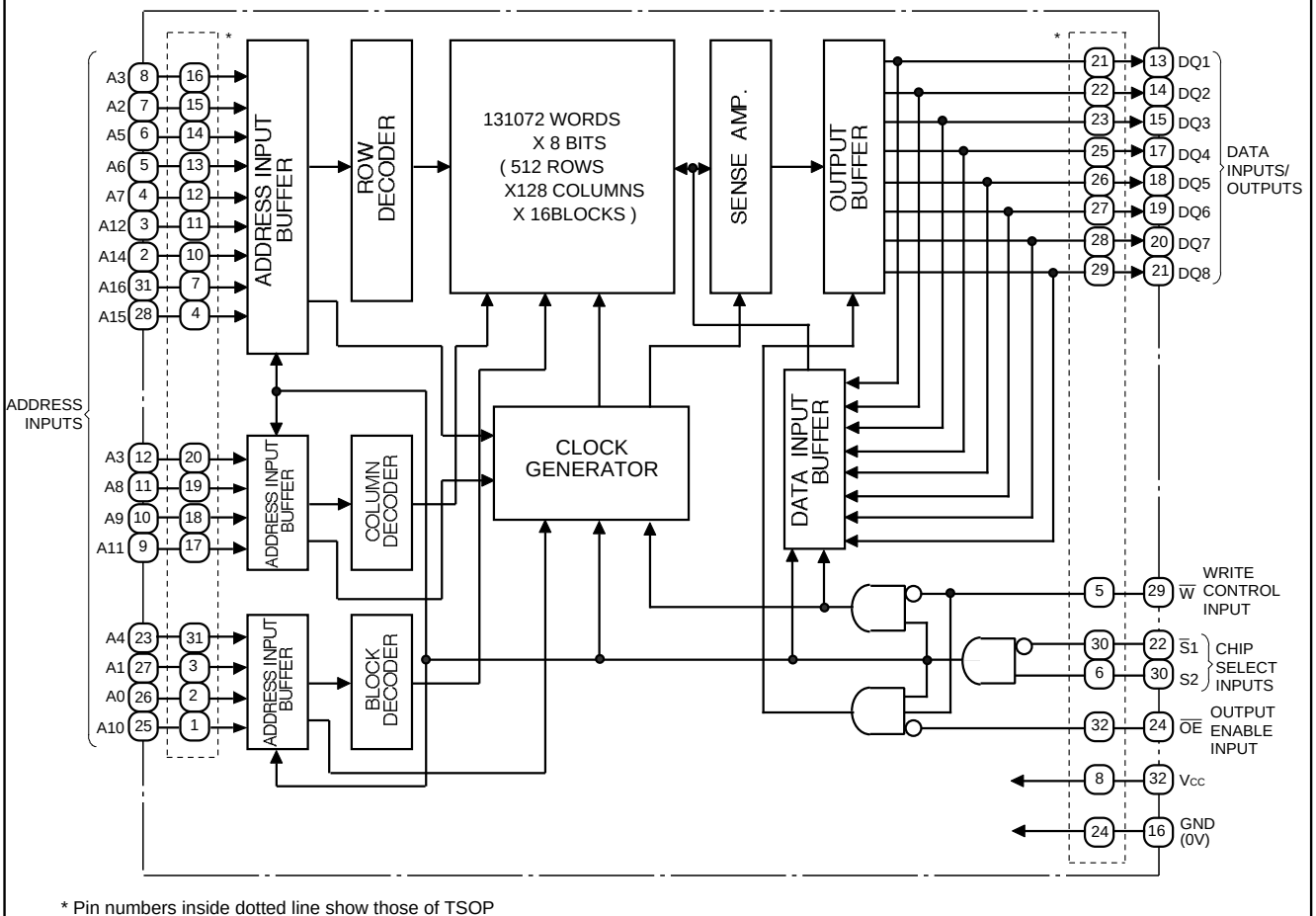
A read cycle is executed by setting $\overline{W}$ at a high level and $\overline{OE}$ at a low level while $\overline{S}_1$ and S_2 are in an active state($\overline{S}_1$=L,S_2=H).

FUNCTION TABLE

$\overline{S}_1$	S_2	$\overline{W}$	$\overline{OE}$	Mode	DQ	I_{CC}
X	L	X	X	Non selection	High-impedance	Stand-by
H	X	X	X	Non selection	High-impedance	Stand-by
L	H	L	X	Write	Din	Active
L	H	H	L	Read	Dout	Active
L	H	H	H		High-impedance	Active

When setting $\overline{S}_1$ at a high level or S_2 at a low level, the chip are in a non-selectable mode in which both reading and writing are disabled. In this mode, the output stage is in a high- impedance state, allowing OR-tie with other chips and memory expansion by $\overline{S}_1$ and S_2. The power supply current is reduced as low as the stand-by current which is specified as I_{CC3} or I_{CC4}, and the memory data can be held at +2V power supply, enabling battery back-up operation during power failure or power-down operation in the non-selected mode.

BLOCK DIAGRAM



* Pin numbers inside dotted line show those of TSOP

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Conditions	Ratings	Unit
V_{CC}	Supply voltage	With respect to GND	– 0.3*~4.6	V
V_I	Input voltage		– 0.3*~Vcc + 0.3 (Max 4.6)	V
V_O	Output voltage		0~Vcc	V
P_d	Power dissipation	Ta=25°C	700	mW
T_{opr}	Operating temperature		0~70	°C
T_{stg}	Storage temperature		– 65~150	°C

* –3.0V in case of AC (Pulse width ≤ 30ns)

DC ELECTRICAL CHARACTERISTICS (Ta=0~70°C, Vcc=2.7~3.6V, unless otherwise noted)

Symbol	Parameter	Test conditions			Limits Min	Limits Typ	Limits Max	Unit
V_{IH}	High-level input voltage				2.0		Vcc + 0.3	V
V_{IL}	Low-level input voltage				–0.3*		0.6	V
V_{OH1}	High-level output voltage 1	I_{OH}= – 0.5mA			2.4			V
V_{OH2}	High-level output voltage 2	I_{OH}= – 0.05mA			Vcc – 0.5			V
V_{OL}	Low-level output voltage	I_{OL}= 2mA					0.4	V
I_I	Input current	V_I=0~Vcc					±1	µA
I_O	Output current in off-state	$\overline{S_1}$=V_{IH} or S_2=V_{IL} or $\overline{OE}$=V_{IH} $V_{I/O}$=0~V_{CC}					±1	µA
I_{CC1}	Active supply current	$\overline{S_1}$=V_{IL},S_2=V_{IH}, other inputs=V_{IH} or V_{IL} Output-open(duty 100%)		70ns			35	
I_{CC2}	Active supply current			1MHz			5	
I_{CC3}	Stand-by current	1) S_2 ≤ 0.2V other inputs=0~V_{CC} 2) $\overline{S_1}$ ≥ V_{CC}–0.2V, S_2 ≥ V_{CC}–0.2V other inputs=0~V_{CC}	-H	~25°C			1.2	µA
				~40°C			3.6	
				~70°C			12	
I_{CC4}	Stand-by current	$\overline{S_1}$=V_{IH} or S_2=V_{IL}, other inputs=0~V_{CC}					0.33	mA

* –3.0V in case of AC (Pulse width ≤ 30ns)

CAPACITANCE (Ta=0~70°C, unless otherwise noted)

Symbol	Parameter	Test conditions	Limits Min	Limits Typ	Limits Max	Unit
C_I	Input capacitance	V_I=GND, V_I=25mVrms, f=1MHz			8	pF
C_O	Output capacitance	V_O=GND,V_O=25mVrms, f=1MHz			10	pF

Note 1: Direction for current flowing into an IC is positive (no mark).

2: Typical value is Vcc = 3V, Ta = 25°C

AC ELECTRICAL CHARACTERISTICS (Ta=0~70°C, unless otherwise noted)

(1) MEASUREMENT CONDITIONS

V_{CC} ····· 2.7~3.6V
Input pulse level ····· V_{IH}=2.2V,V_{IL}=0.4V
Input rise and fall time ····· 5ns
Reference level ····· V_{OH}=V_{OL}=1.5V
Output loads ····· Fig.1, C_L=30pF
C_L=5pF (for t_{en},t_{dis})
Transition is measured ± 500mV from steady state voltage. (for t_{en},t_{dis})

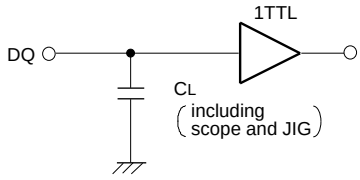


Fig.1 Output load

(2) READ CYCLE

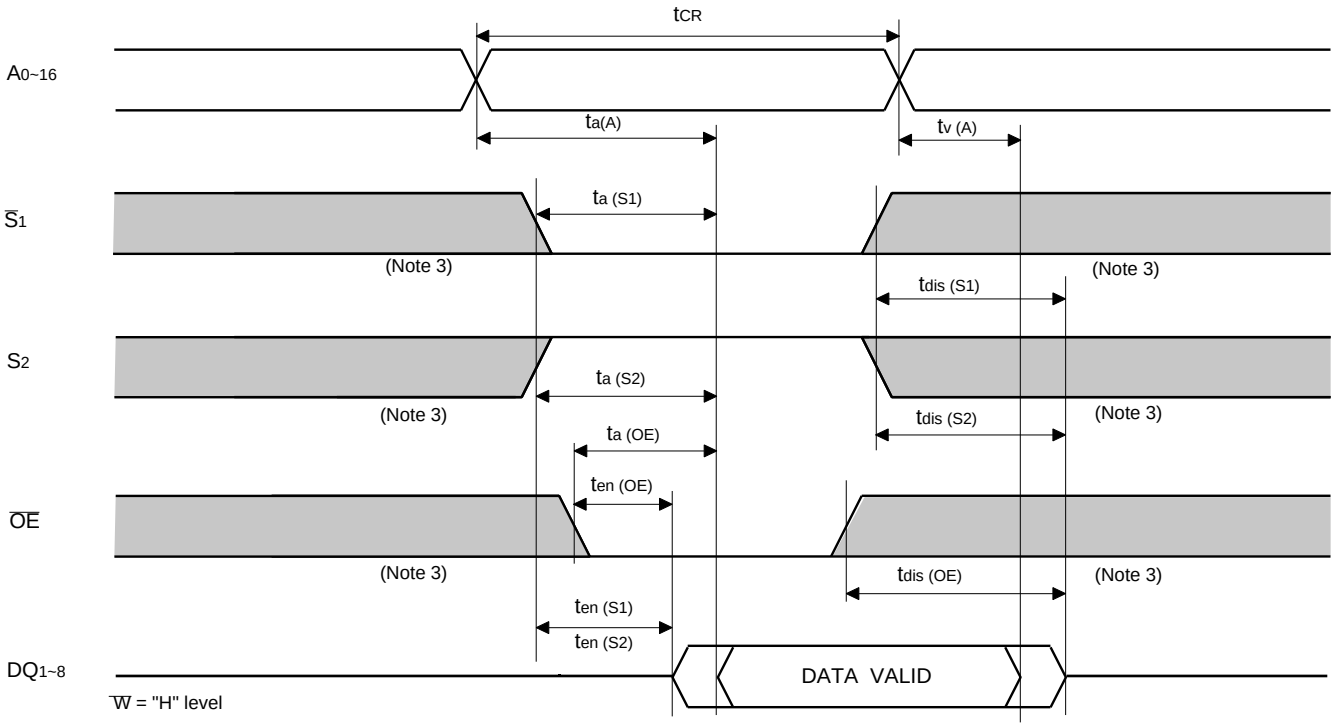
Symbol	Parameter	Limits		Unit
		-70H		
		Min	Max	
t_{CR}	Read cycle time	70		ns
$t_{a(A)}$	Address access time		70	ns
$t_{a(S1)}$	Chip select 1 access time		70	ns
$t_{a(S2)}$	Chip select 2 access time		70	ns
$t_{a(OE)}$	Output enable access time		35	ns
$t_{dis(S1)}$	Output disable time after $\overline{S_1}$ high		25	ns
$t_{dis(S2)}$	Output disable time after S_2 low		25	ns
$t_{dis(OE)}$	Output disable time after $\overline{OE}$ high		25	ns
$t_{en(S1)}$	Output enable time after $\overline{S_1}$ low	10		ns
$t_{en(S2)}$	Output enable time after S_2 high	10		ns
$t_{en(OE)}$	Output enable time after $\overline{OE}$ low	5		ns
$t_{V(A)}$	Data valid time after address	10		ns

(3) WRITE CYCLE

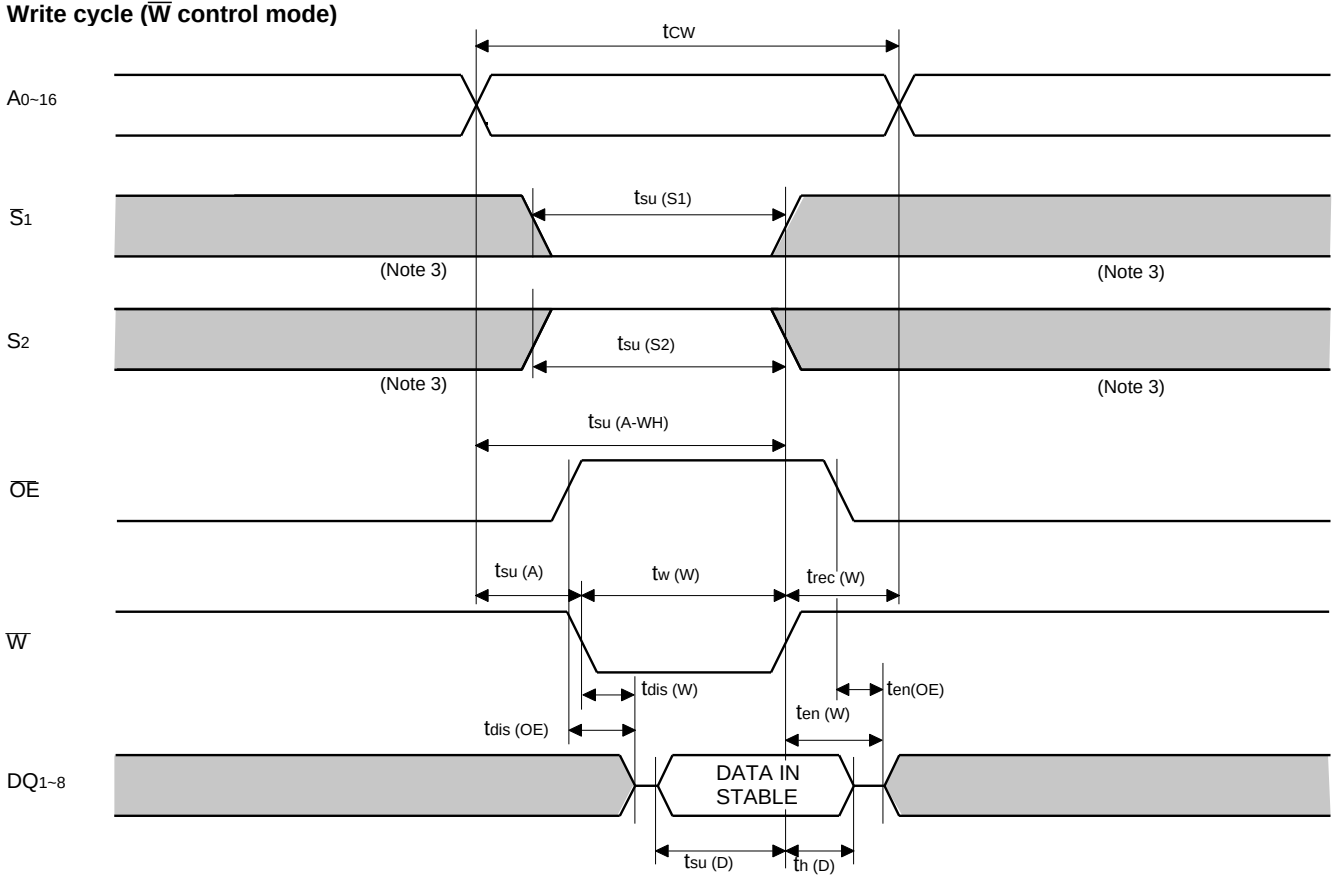
Symbol	Parameter	Limits		Unit
		-70H		
		Min	Max	
t_{CW}	Write cycle time	70		ns
$t_{w(W)}$	Write pulse width	55		ns
$t_{su(A)}$	Address setup time	0		ns
$t_{su(A-WH)}$	Address setup time with respect to $\overline{W}$	65		ns
$t_{su(S1)}$	Chip select 1 setup time	65		ns
$t_{su(S2)}$	Chip select 2 setup time	65		ns
$t_{su(D)}$	Data setup time	30		ns
$t_{h(D)}$	Data hold time	0		ns
$t_{rec(W)}$	Write recovery time	0		ns
$t_{dis(W)}$	Output disable time from $\overline{W}$ low		25	ns
$t_{dis(OE)}$	Output disable time from $\overline{OE}$ high		25	ns
$t_{en(W)}$	Output enable time from $\overline{W}$ high	5		ns
$t_{en(OE)}$	Output enable time from $\overline{OE}$ low	5		ns

(4) TIMING DIAGRAMS

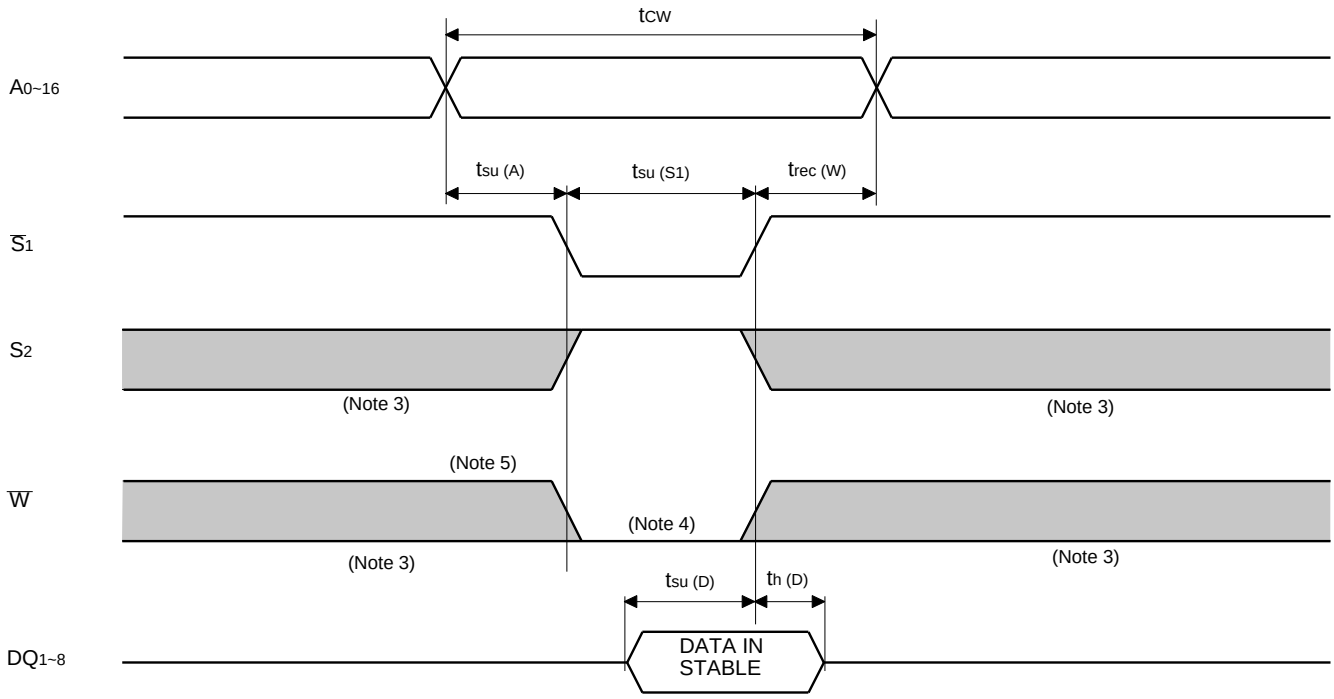
Read cycle



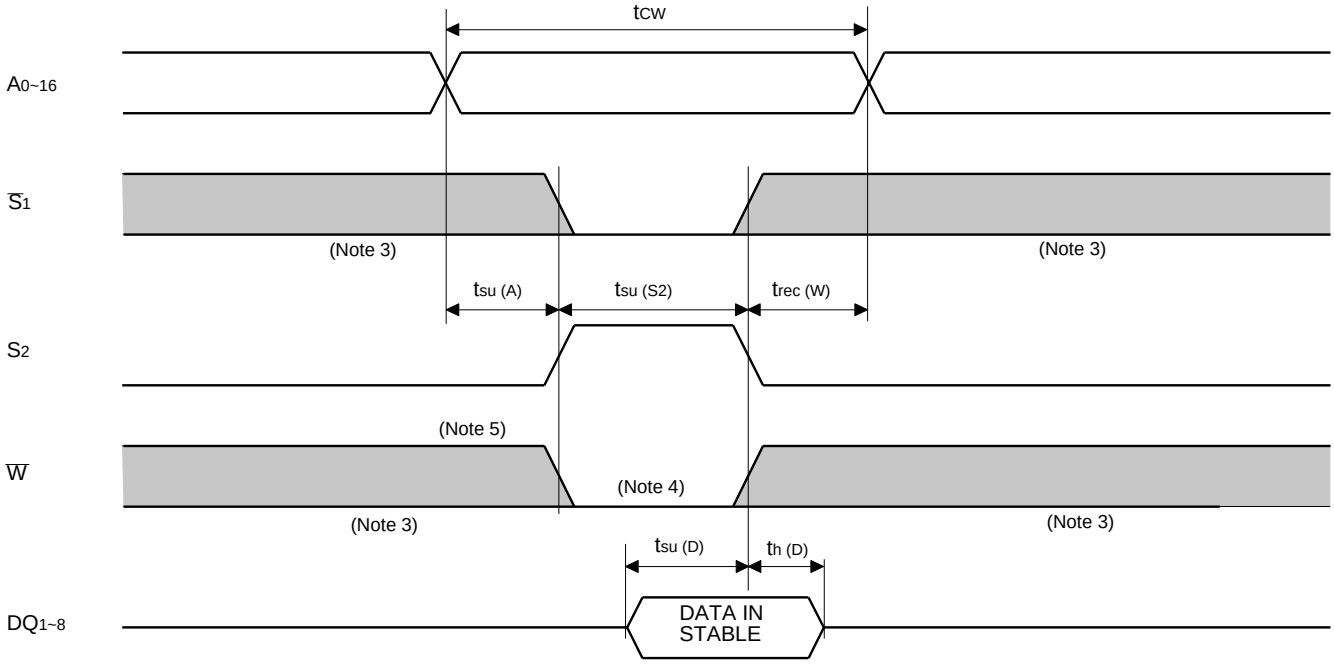
Write cycle ($\overline{W}$ control mode)



Write cycle ($\overline{S}_1$ control mode)



Write cycle (S_2 control mode)



Note 3: Hatching indicates the state is "don't care".
4: Writing is executed while S_2 high overlaps $\overline{S}_1$ and $\overline{W}$ low.
5: When the falling edge of $\overline{W}$ is simultaneously or prior to the falling edge of $\overline{S}_1$ or rising edge of S_2, the outputs are maintained in the high impedance state.
6: Don't apply inverted phase signal externally when DQ pin is output mode.

POWER DOWN CHARACTERISTICS

(1) ELECTRICAL CHARACTERISTICS (Ta=0~70°C, unless otherwise noted)

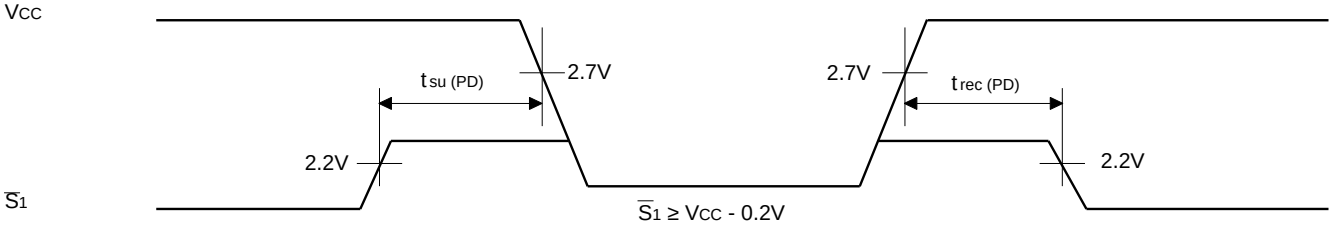
Symbol	Parameter	Test conditions			Limits			Unit
					Min	Typ	Max	
$V_{CC\ (PD)}$	Power down supply voltage				2			V
$V_{I\ (S1)}$	Chip select input $\overline{S_1}$				2.0	Vcc(PD)		V
$V_{I\ (S2)}$	Chip select input S_2	2.7V≤Vcc(PD)					0.6	V
		Vcc(PD)<2.7V					0.2	V
$I_{CC\ (PD)}$	Power down supply current	V_{CC} = 3V 1) $S_2 \leq 0.2V$, other inputs = 0~3V 2) $\overline{S_1} \geq V_{CC}-0.2V$, $S_2 \geq V_{CC}-0.2V$ other inputs = 0~3V	-H	~25°C			1	µA
				~40°C			3	
				~70°C			10	

(2) TIMING REQUIREMENTS (Ta=0~70°C, unless otherwise noted)

Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
$t_{su\ (PD)}$	Power down set up time		0			ns
$t_{rec\ (PD)}$	Power down recovery time		5			ms

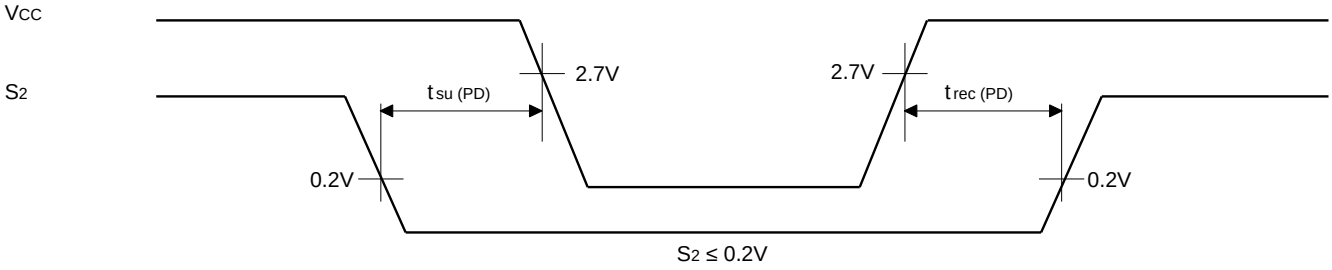
(3) POWER DOWN CHARACTERISTICS

$\overline{S_1}$ control mode



Note 7: On the power down mode by controlling $\overline{S_1}$,the input level of S_2 must be $S_2 \geq$ Vcc - 0.2V or $S_2 \leq 0.2V$. The other pins(Address,I/O,$\overline{WE}$,$\overline{OE}$) can be in high impedance state.

S_2 control mode



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